

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AJT006** is Designed for
9 – 1215 MHz, JTIDS Applications.

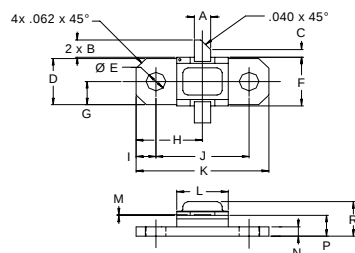
FEATURES:

- Internal Input/Output Matching Network
- $P_G = 9.3$ dB at 6.0 W/1215 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.9 A
V_{CC}	32V
P_{DISS}	25 W @ $T_C \leq 75^\circ C$
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	7.0 °C/W

PACKAGE STYLE .310 2L FLG



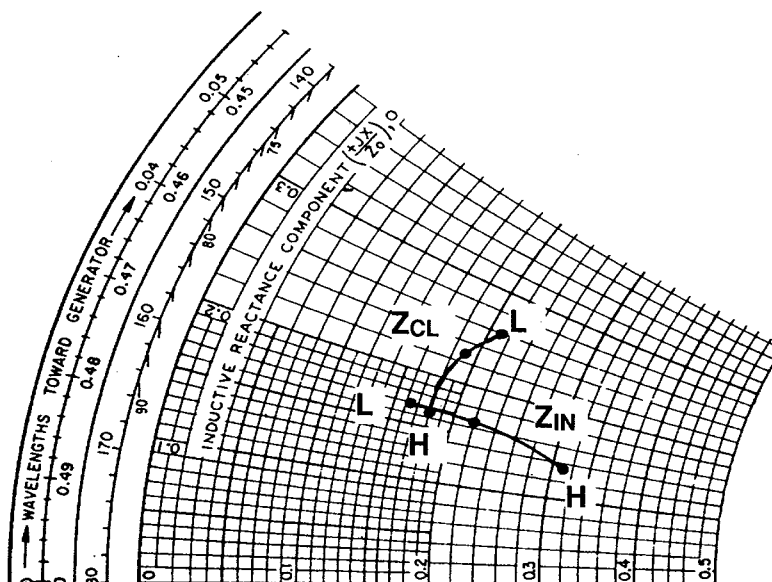
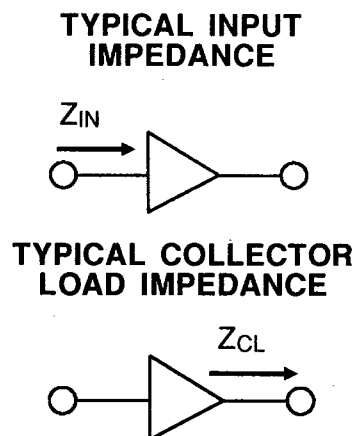
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.286 / 7.26	.306 / 7.77
E	.110 / 2.79	.130 / 3.30
F	.306 / 7.77	.318 / 8.08
G	.148 / 3.76	
H	.400 / 10.16	
I	.119 / 3.02	
J	.552 / 14.02	.572 / 14.53
K	.790 / 20.07	.810 / 20.57
L	.300 / 7.62	.320 / 8.13
M	.003 / 0.08	.006 / 0.15
N	.052 / 1.32	.072 / 1.83
P	.118 / 3.00	.131 / 3.33
R		.230 / 5.84

ORDER CODE: ASI10544

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	48			V
BV_{CER}	$I_C = 5.0$ mA $R_{BE} = 10 \Omega$	48			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 28$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	30		300	---
P_G	$V_{CC} = 45$ V $P_{OUT} = 6.0$ W $f = 960$ -1215 MHz	9.3			dB
η_c		40			%

IMPEDANCE DATA



FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
960 MHZ	$8.2 + j8.52$	$10.5 + j12.9$
1090 MHZ	$11.1 + j8.34$	$9.4 + j11.3$
1215 MHZ	$15.6 + j6.8$	$9.0 + j8.3$

 $P_{IN} = 0.7 \text{ W}$
 $V_{CC} = 28 \text{ V}$